

## OptiMOS® Power-Transistor

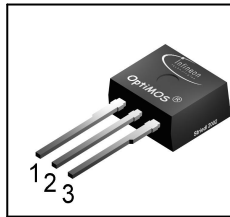
### Feature

- N-Channel
- Enhancement mode
- Logic Level
- Avalanche rated
- $dv/dt$  rated

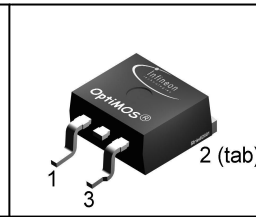
### Product Summary

$V_{DS}$	55	V
$R_{DS(on)}$ max. SMD version	4.5	m $\Omega$
$I_D$	80	A

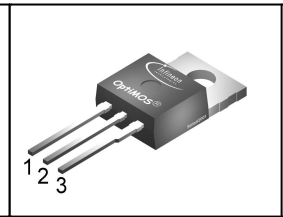
P- TO262 -3-1



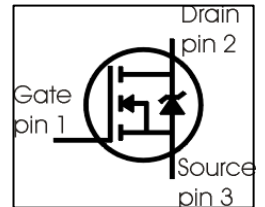
P- TO263 -3-2



P- TO220 -3-1



Type	Package	Ordering Code	Marking
SPP80N06S2L-05	P- TO220 -3-1	Q67040-S4246	2N06L05
SPB80N06S2L-05	P- TO263 -3-2	Q67040-S4256	2N06L05
SPI80N06S2L-05	P- TO262 -3-1	Q67060-S7422	2N06L05



### Maximum Ratings, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current 1) $T_C=25^\circ\text{C}$	$I_D$	80 80	A
Pulsed drain current $T_C=25^\circ\text{C}$	$I_{D \text{ puls}}$	320	
Avalanche energy, single pulse $I_D=80 \text{ A}$ , $V_{DS}=25\text{V}$ , $R_{GS}=25\Omega$	$E_{AS}$	800	mJ
Repetitive avalanche energy, limited by $T_{jmax}^{2)}$	$E_{AR}$	30	
Reverse diode $dv/dt$ $I_S=80\text{A}$ , $V_{DS}=44\text{V}$ , $di/dt=200\text{A}/\mu\text{s}$ , $T_{jmax}=175^\circ\text{C}$	$dv/dt$	6	kV/ $\mu\text{s}$
Gate source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation $T_C=25^\circ\text{C}$	$P_{tot}$	300	W
Operating and storage temperature	$T_j, T_{stg}$	-55... +175	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/175/56	

## Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	$R_{thJC}$	-	0.3	0.5	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62	
SMD version, device on PCB:	$R_{thJA}$				
@ min. footprint		-	-	62	
@ 6 cm <sup>2</sup> cooling area <sup>3)</sup>		-	-	40	

## Electrical Characteristics, at $T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS}=0V, I_D=1mA$	$V_{(BR)DSS}$	55	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=250\mu A$	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current $V_{DS}=55V, V_{GS}=0V, T_j=25^{\circ}C$ $V_{DS}=55V, V_{GS}=0V, T_j=125^{\circ}C^2)$	$I_{DSS}$	- -	0.01 1	1 100	$\mu A$
Gate-source leakage current $V_{GS}=20V, V_{DS}=0V$	$I_{GSS}$	-	1	100	
Drain-source on-state resistance $V_{GS}=4.5V, I_D=80A$ $V_{GS}=4.5V, I_D=80A, SMD\ version$	$R_{DS(on)}$	- -	4.4 4.1	6 5.7	m $\Omega$
Drain-source on-state resistance4) $V_{GS}=10V, I_D=80A$ $V_{GS}=10V, I_D=80A, SMD\ version$	$R_{DS(on)}$	- -	3.6 3.3	4.8 4.5	

<sup>1</sup>Current limited by bondwire ; with an  $R_{thJC} = 0.5K/W$  the chip is able to carry  $I_D = 173A$  at  $25^\circ\text{C}$ , for detailed information see app.-note ANPS071E available at [www.infineon.com/optimos](http://www.infineon.com/optimos)

<sup>2</sup>Defined by design. Not subject to production test.

<sup>3</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu m$  thick) copper area for drain connection. PCB is vertical without blown air.

<sup>4</sup>Diagrams are related to straight lead versions

### Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

### Dynamic Characteristics

Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 80A$	76	152	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0V$ , $V_{DS} = 25V$ , $f = 1MHz$	-	5700	7530	pF
Output capacitance	$C_{oss}$		-	1330	1760	
Reverse transfer capacitance	$C_{rss}$		-	360	540	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 30V$ , $V_{GS} = 10V$ , $I_D = 80A$ , $R_G = 1.3\Omega$	-	25	38	ns
Rise time	$t_r$		-	93	140	
Turn-off delay time	$t_{d(off)}$		-	67	100	
Fall time	$t_f$		-	90	135	

### Gate Charge Characteristics

Gate to source charge	$Q_{gs}$	$V_{DD} = 44V$ , $I_D = 80A$	-	19	25	nC
Gate to drain charge	$Q_{gd}$		-	60	90	
Gate charge total	$Q_g$	$V_{DD} = 44V$ , $I_D = 80A$ , $V_{GS} = 0$ to $10V$	-	170	230	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 44V$ , $I_D = 80A$	-	3.3	-	V

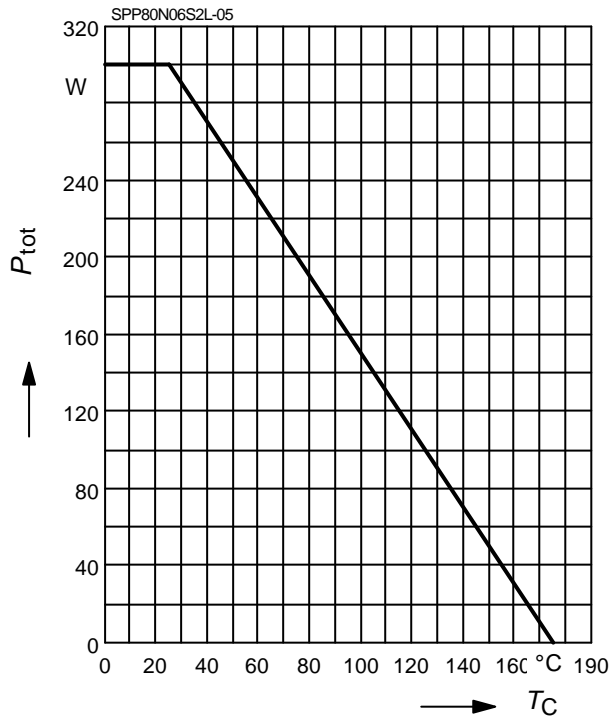
### Reverse Diode

Inverse diode continuous forward current	$I_S$	$T_C = 25^\circ C$	-	-	80	A
Inv. diode direct current, pulsed	$I_{SM}$		-	-	320	
Inverse diode forward voltage	$V_{SD}$	$V_{GS} = 0V$ , $I_F = 80A$	-	0.9	1.3	V
Reverse recovery time	$t_{rr}$	$V_R = 30V$ , $I_F = I_S$ , $di_F/dt = 100A/\mu s$	-	65	80	ns
Reverse recovery charge	$Q_{rr}$		-	125	160	nC

### 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$

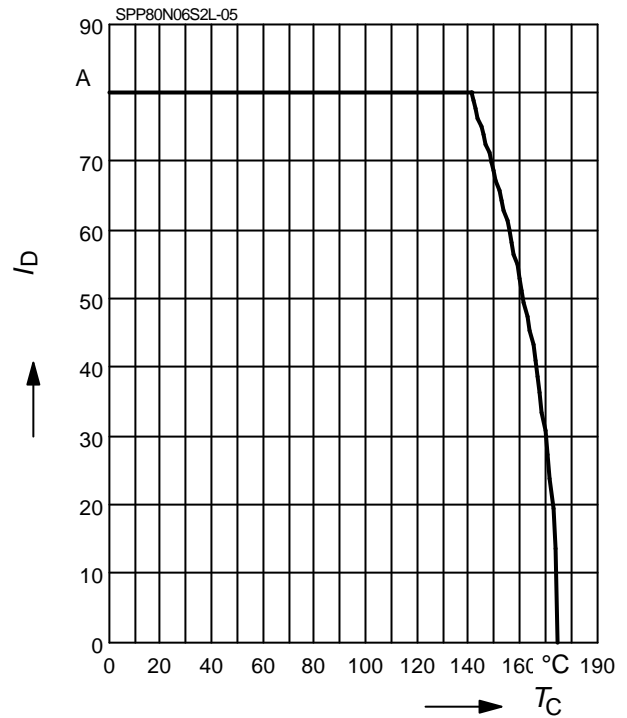
parameter:  $V_{GS} \geq 4 \text{ V}$



### 2 Drain current

$$I_D = f(T_C)$$

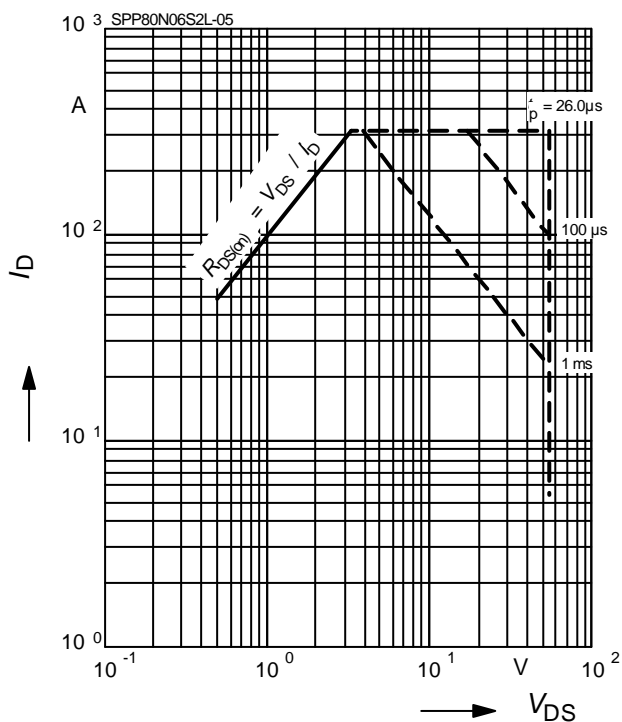
parameter:  $V_{GS} \geq 10 \text{ V}$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

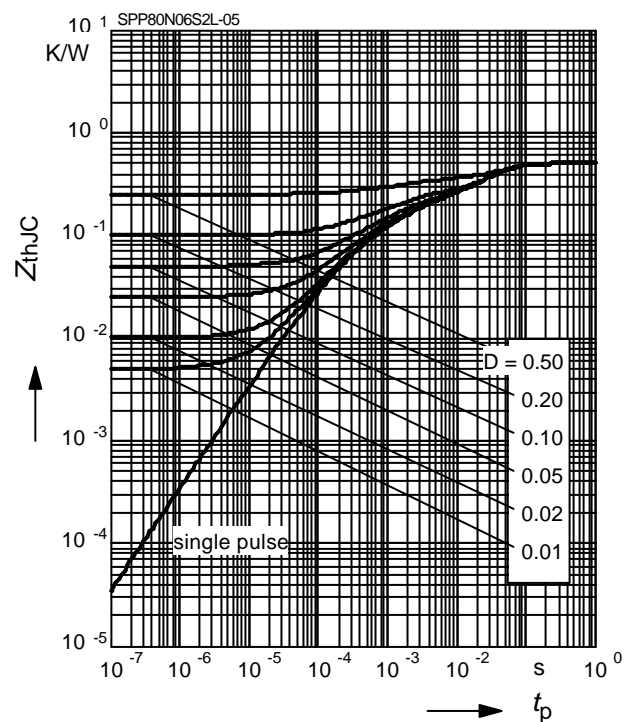
parameter:  $D = 0$ ,  $T_C = 25^\circ\text{C}$



### 4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

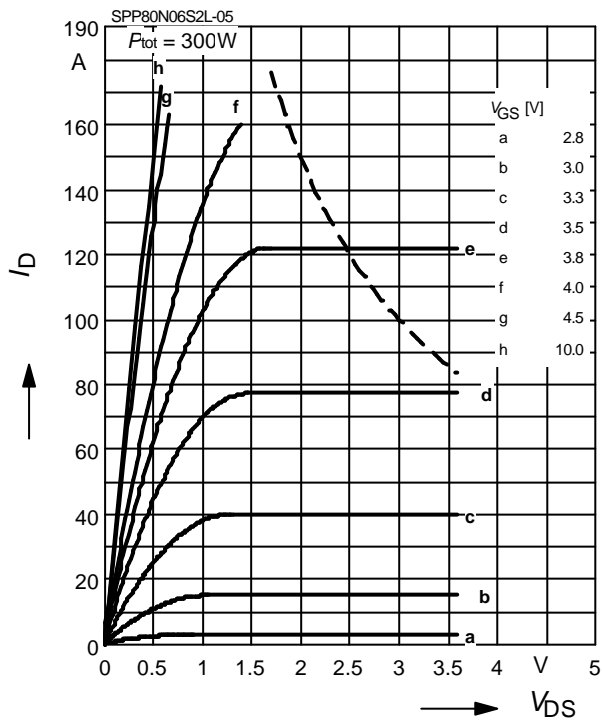
parameter:  $D = t_p/T$



### 5 Typ. output characteristic

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

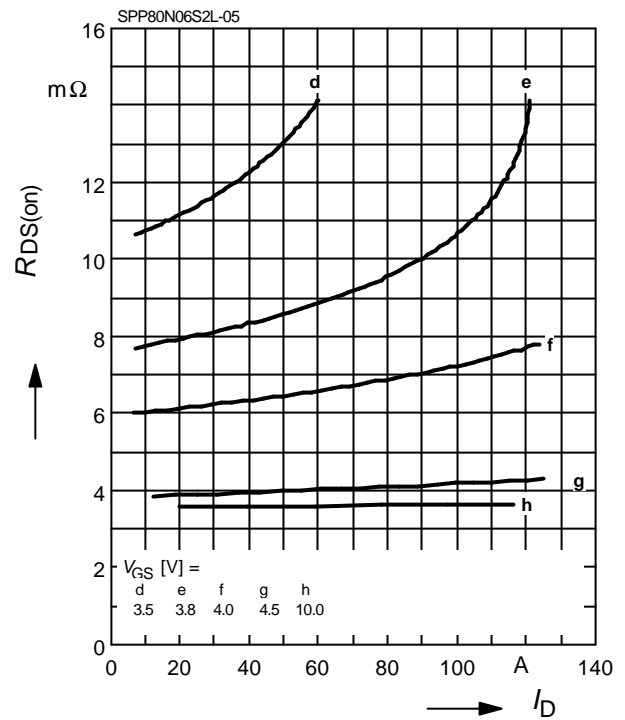
parameter:  $t_p = 80 \mu\text{s}$



### 6 Typ. drain-source on resistance

$$R_{DS(\text{on})} = f(I_D)$$

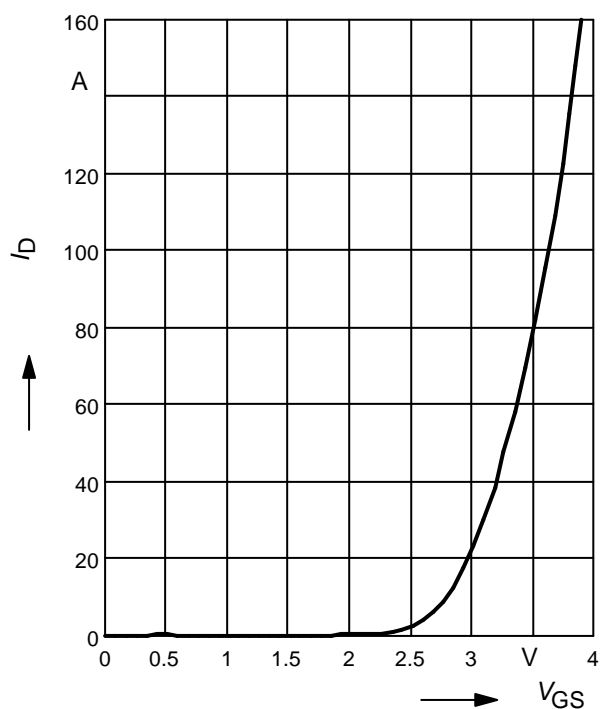
parameter:  $V_{GS}$



### 7 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(\text{on})\text{max}}$$

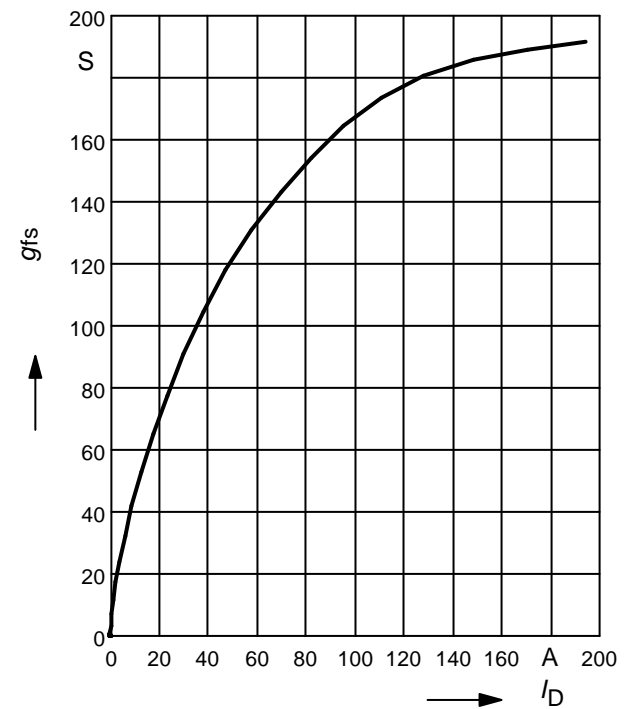
parameter:  $t_p = 80 \mu\text{s}$



### 8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$$

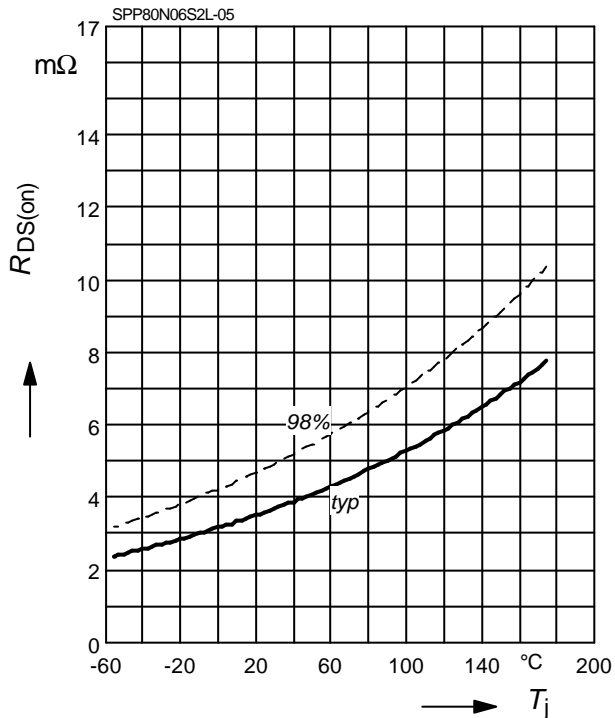
parameter:  $g_{fs}$



## 9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

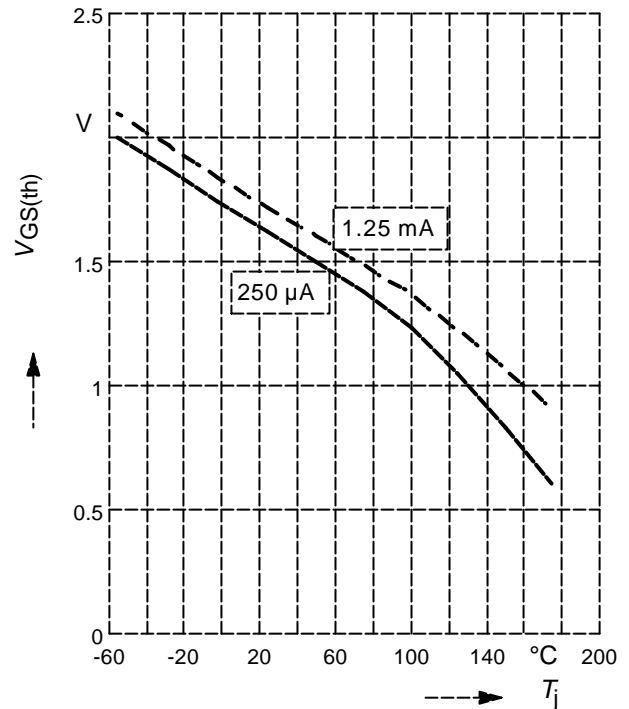
parameter:  $I_D = 80\text{ A}$ ,  $V_{GS} = 10\text{ V}$



## 10 Typ. gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

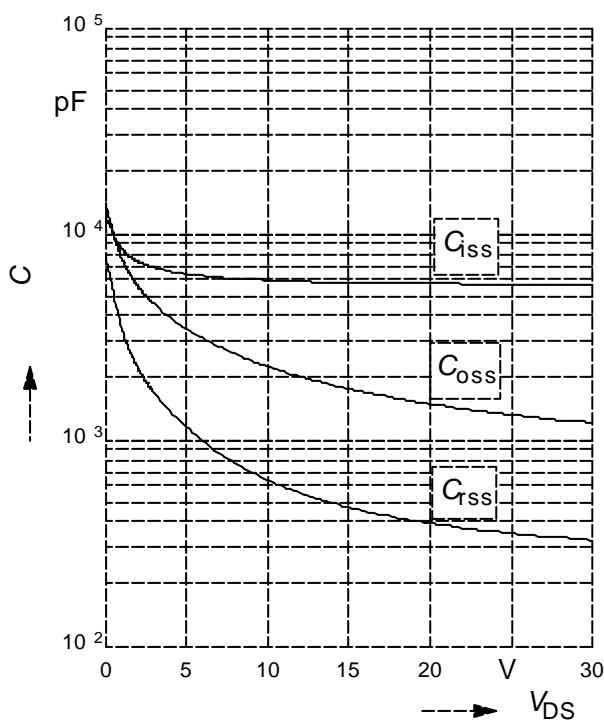
parameter:  $V_{GS} = V_{DS}$



## 11 Typ. capacitances

$$C = f(V_{DS})$$

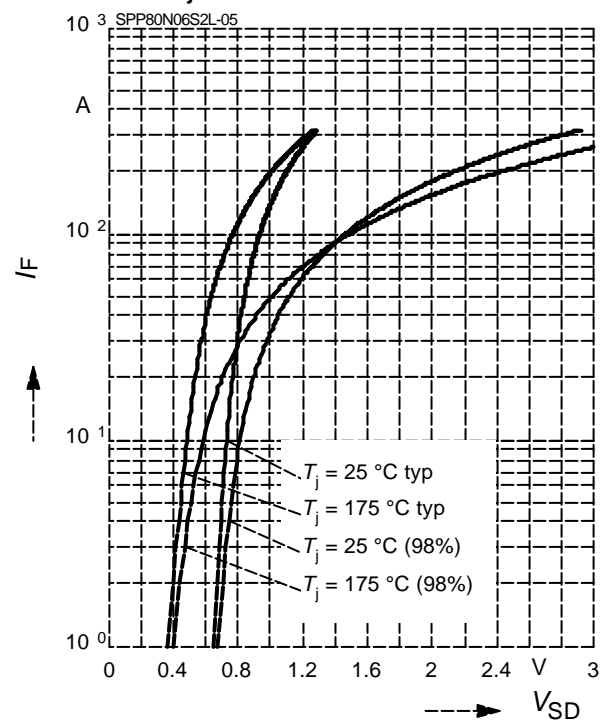
parameter:  $V_{GS} = 0\text{ V}$ ,  $f = 1\text{ MHz}$



## 12 Forward character. of reverse diode

$$I_F = f(V_{SD})$$

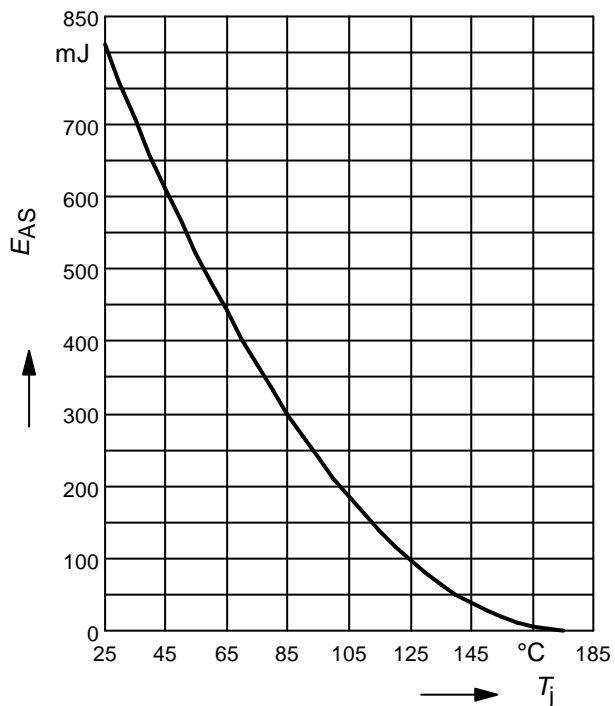
parameter:  $T_j$ ,  $t_p = 80\text{ μs}$



### 13 Typ. avalanche energy

$$E_{AS} = f(T_j)$$

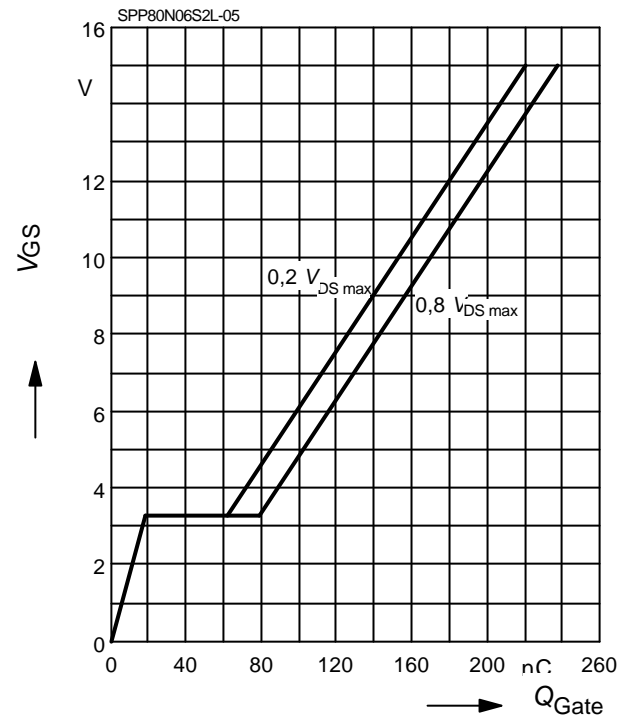
par.:  $I_D = 80\text{ A}$ ,  $V_{DD} = 25\text{ V}$ ,  $R_{GS} = 25\ \Omega$



### 14 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

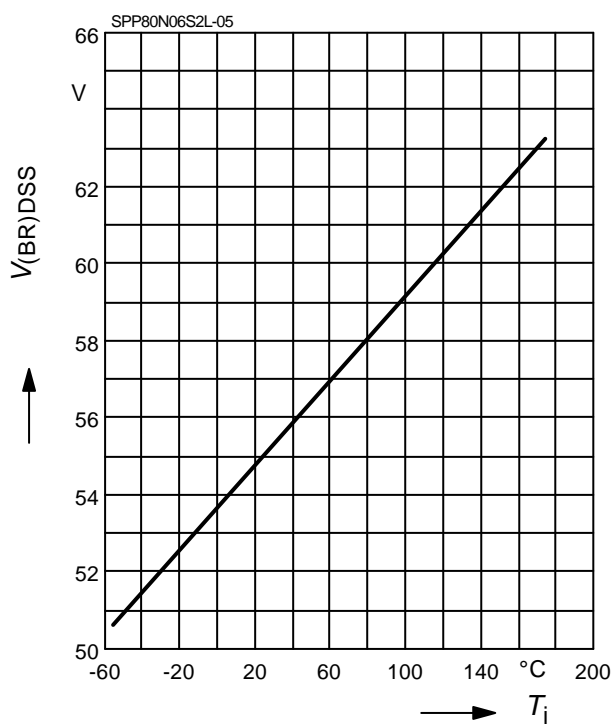
parameter:  $I_D = 80\text{ A}$  pulsed



### 15 Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$

parameter:  $I_D = 10\text{ mA}$



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**Further information**

Please notice that the part number is **BSPP80N06S2L-05** and **BSPB80N06S2L-05**, for simplicity the device is referred to by the term **SPP80N06S2L-05** and **SPB80N06S2L-05** throughout this documentation.